

AP3015/A

#### **General Description**

The AP3015/A are Pulse Frequency Modulation (PFM) DC/DC converters. These two devices are functionally equivalent except the switching current limit. The AP3015 is designed for higher power systems with 350mA current limit, and the AP3015A is for lower power systems with 100mA current limit.

The AP3015/A feature a wide input voltage. The operation voltage is ranged from 1.2Vto 12V (1V to 12V for AP3015A). A current limited, fixed off-time control scheme conserves operating current, resulting in high efficiency over a broad range of load current. They also feature low quiescent current, switching current limiting, low temperature coefficient, etc.

Fewer tiny external components are required in the applications to save space and lower cost. Furthermore, to ease its use in different systems, a disable terminal is designed to turn on or turn off the chip.

The AP3015/A are available in SOT-23-5 package.

#### **Features**

- Low Quiescent Current
   In Active Mode (Not Switching): 17μA Typical
   In Shutdown Mode: <1μA</li>
- Low Operating V<sub>IN</sub>
   1.2V Typical for AP3015
   1.0V Typical for AP3015A
- Low V<sub>CESAT</sub> Switch 200mV Typical at 300mA for AP3015 70mV Typical at 70mA for AP3015A
- High Output Voltage: up to 34V
- · Fixed Off-Time Control
- Switching Current Limiting 350mA Typical for AP3015 100mA Typical for AP3015A
- Operating Temperature Range: -40°C to 85°C

### **Applications**

- MP3, MP4
- Battery Power Supply System
- LCD/OLED Bias Supply
- Handheld Device
- Portable Communication Device

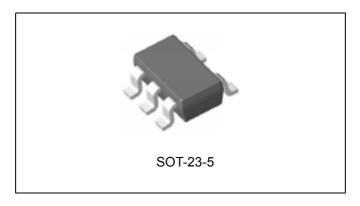


Figure 1. Package Type of AP3015/A



AP3015/A

## **Pin Configuration**

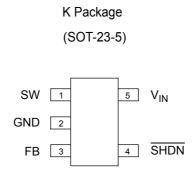


Figure 2. Pin Configuration of AP3015/A (Top View)

# **Pin Description**

Pin Number	Pin Name	Function
1	SW	Switch Pin. This is the collector of the internal NPN power switch. Minimize the trace area connected to this Pin to minimize EMI
2	GND	Ground Pin. GND should be tied directly to ground plane for best performance
3	FB	Feedback Pin. Set the output voltage through this pin. The formula is V <sub>OUT</sub> =1.23V*(1+R1/R2). Keep the loop between Vout and FB as short as possible to minimize the ripple and noise, which is beneficial to the stability and output ripple
4	SHDN	Shutdown Control Pin. Tie this pin above 0.9V to enable the device. Tie below 0.25V to turn off the device
5	V <sub>IN</sub>	Supply Input Pin. Bypass this pin with a capacitor as close to the device as possible



### **Functional Block Diagram**

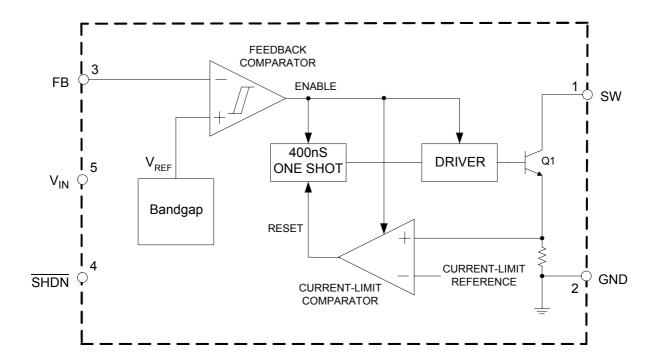
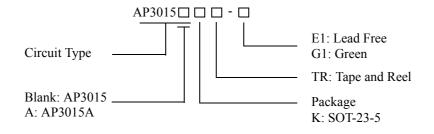


Figure 3. Functional Block Diagram of AP3015/A

### **Ordering Information**



Package	Temperature	Part Number		Marking ID		Packing Type	
	Range	Lead Free	Green	Lead Free	Green	racking Type	
SOT-23-5	-40 to 85°C	AP3015KTR-E1	AP3015KTR-G1	E6E	G6E	Tape & Reel	
		AP3015AKTR-E1	AP3015AKTR-G1	E6F	G6F	Tape & Reel	

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green package.



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### **Absolute Maximum Ratings (Note 1)**

Parameter	Symbol	Value	Unit
Input Voltage	V <sub>IN</sub>	15	V
SW Voltage	$V_{SW}$	38	V
FB Voltage	$V_{FB}$	V <sub>IN</sub>	V
SHDN Pin Voltage	V <sub>SHDN</sub>	15	V
Thermal Resistance (Junction to Ambient, no Heat sink)	$R_{ heta JA}$	265	°C/W
Operating Junction Temperature	$T_{J}$	150	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°С
Lead Temperature (Soldering, 10sec)	$T_{LEAD}$	260	°C
ESD (Human Body Model)		3000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

### **Recommended Operating Conditions**

Parameter	Symbol		Min	Max	Unit
Input Voltage	V	AP3105	1.2	12	V
imput voitage	$v_{\mathrm{IN}}$	AP3105A	1.0	12	v
Operating Temperature	$T_{A}$		-40	85	°C



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### **Electrical Characteristics**

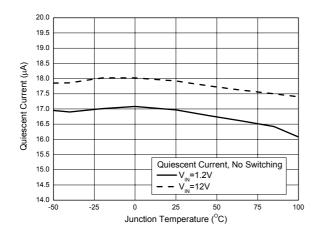
 $(V_{IN}=V_{\overline{SHDN}}=1.2V, T_A=25^{o}C, unless otherwise specified.)$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Input Voltage	$V_{IN}$	AP3015	1.2		12	- V	
imput voitage	* IN	AP3015A	1.0		12		
Quiescent Current	I <sub>Q</sub>	Not Switching		17	30	μА	
Quiescent current		V <sub>SHDN</sub> =0V			1		
Feedback Voltage	$V_{\mathrm{FB}}$		1.205	1.23	1.255	V	
FB Comparator Hysteresis	$V_{\mathrm{FBH}}$			8		mV	
FB Pin Bias Current	$I_{FB}$	V <sub>FB</sub> =1.23V		30	80	nA	
Output Voltage Line Regulation	$L_{NR}$	1.2V <v<sub>IN&lt;12V</v<sub>		0.05	0.1	%/V	
Switching Current Limit	$I_{ m L}$	AP3015	300	350	400	mA	
Switching Current Limit	1L	AP3015A	75	100	125		
Switch Saturation Voltage	V <sub>CESAT</sub>	AP3015, I <sub>SW</sub> =300mA		200	300	- mV	
Switch Saturation Voltage	CESAI	AP3015A, I <sub>SW</sub> =70mA		70	120		
Switch Off Time	T <sub>OFF</sub>	V <sub>FB</sub> >1V		400		nS	
Switch Off Time		V <sub>FB</sub> <0.6V		1.5		μS	
SHDN Input Threshold High	$V_{TH}$		0.9			V	
SHDN Input Threshold Low	V <sub>TL</sub>				0.25	v	
SHDN Pin Current	I	V <sub>SHDN</sub> =1.2V		2	3	- μΑ	
STIDIVI III Culicii	I <sub>SHDN</sub>	V <sub>SHDN</sub> =5V		8	12		
Switch Leakage Current	$I_{SWL}$	Switch Off, V <sub>SW</sub> =5V		0.01	5	μΑ	
Thermal Resistance (Junction to Case)	$\theta_{ m JC}$			52		°C/W	



### **Typical Performance Characteristics**

Unless otherwise noted,  $V_{IN}=1.2V$ 



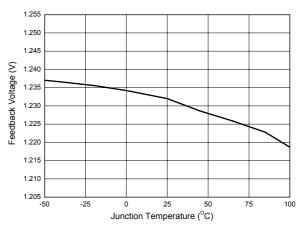
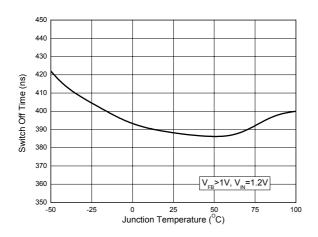


Figure 4. Quiescent Current vs. Junction Temperature

Figure 5. Feedback Voltage vs. Junction Temperature



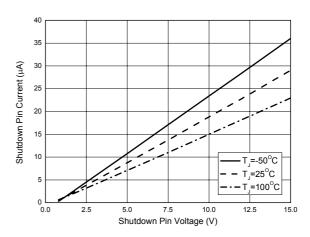
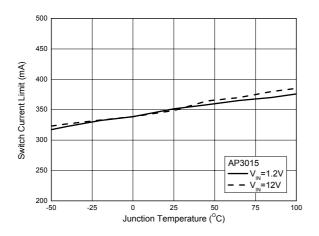


Figure 6. Switch Off Time vs. Junction Temperature Figure 7. Shutdown Pin Current vs. Shutdown Pin Voltage

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### **Typical Performance Characteristics (Continued)**

Unless otherwise noted,  $V_{IN}=1.2V$ 



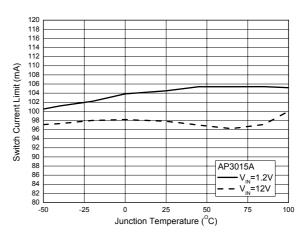
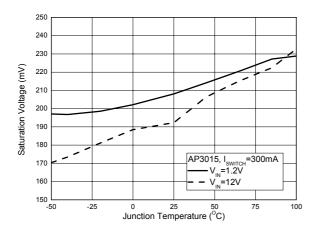


Figure 8. Switch Current Limit vs. Junction Temperature Figure 9. Switch Current Limit vs. Junction Temperature



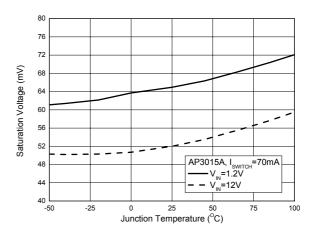
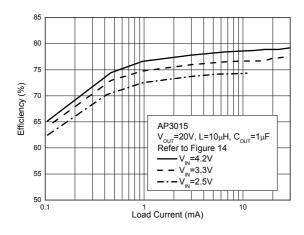


Figure 10. Saturation Voltage vs. Junction Temperature Figure 11. Saturation Voltage vs. Junction Temperature



### **Typical Performance Characteristics (Continued)**

Unless otherwise noted, V<sub>IN</sub>=1.2V



AP3015A
V<sub>OUT</sub>=3.3V, L=10μH, C<sub>OUT</sub>=20μF
Refer to Figure 15
— V<sub>N</sub>=2.5V
— - V<sub>N</sub>=1.2V

1 Load Current (mA)

80

Figure 12. Efficiency

## **Application Information**

#### **Operating Principles**

AP3015/A feature a constant off-time control scheme. Refer to Figure 3, the bandgap voltage  $V_{REF}$  (1.23V typical) is used to control the output voltage.

When the voltage at the FB pin drops below the lower hysteresis point of Feedback Comparator (typical hysteresis is 8mV), the Feedback Comparator enables the chip and the NPN power switch is turned on, the current in the inductor begins to ramp up and store energy in the coil while the load current is supplied by the output capacitor. Once the current in the inductor reaches the current limit, the Current-Limit Comparator resets the 400ns One-Shot which turns off the NPN switch for 400ns. The SW voltage rises to the output voltage plus a diode drop and the inductor current begins to ramp down. During this time the energy stored in the inductor is transferred to COUT and the load. After the 400ns off-time, the NPN switch is turned on and energy will be stored in the inductor again.

This cycle will continue until the voltage at FB pin reaches 1.23V, the Feedback Comparator disables the

Figure 13. Efficiency

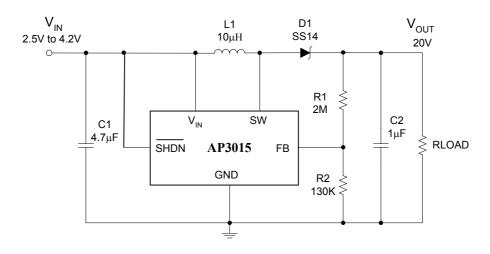
chip and turns off the NPN switch. The load current is then supplied solely by output capacitor and the output voltage will decrease. When the FB pin voltage drops below the lower hysteresis point of Feedback Comparator, the Feedback Comparator enables the device and repeats the cycle described previously. Under not switching condition, the  $I_Q$  of the device is about  $17\mu A.$ 

The AP3015/A contain additional circuitry to provide protection during start-up or under short-circuit conditions. When the FB pin voltage is lower than approximately 0.6V, the switch off-time is increased to 1.5µs and the current limit is reduced to about 250mA (70mA for AP3015A). This reduces the average inductor current and helps to minimize the power dissipation in the AP3015/A power switch, in the external inductor and in the diode.

The SHDN pin can be used to turn off the AP3015/A and reduce the  $I_Q$  to less than  $1\mu A$ . In shutdown mode the output voltage will be a diode drop below the input voltage.



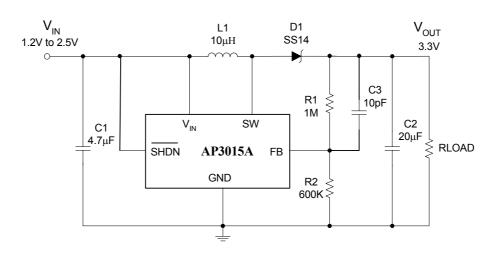
### **Typical Application**



C1, C2: X5R or X7R Ceramic Capacitor

L1: SUMIDA CDRH4D16FB/NP-100MC or Equivalent

Figure 14. AP3015 Typical Application in LCD/OLED Bias Supply



C1, C2, C3: X5R or X7R Ceramic Capacitor

L1: SUMIDA CDRH4D16FB/NP-100MC or Equivalent

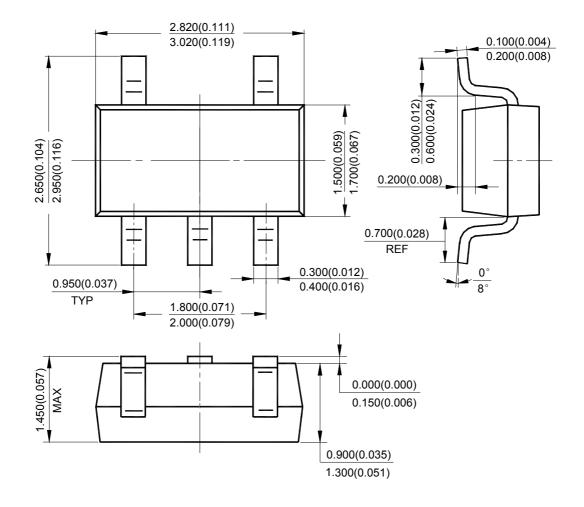
Figure 15. AP3015A Typical Application in 1 or 2 Cells to 3.3V Boost Converter



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#### **Mechanical Dimensions**

SOT-23-5 Unit: mm(inch)







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